

ABSTRACT OF THE DISCLOSURE

Transfer gate (TG) holding trenches are defined in a first interlayer insulating film 44 formed on a silicon substrate 10. TG 33 including side walls 34 are formed in their corresponding
5 trenches. Contact holes are defined in portions adjacent to the TG 33 in a self-aligned manner on the condition that the first interlayer insulating film 44 is selectively removed. Contact plugs 50 are formed in their corresponding contact holes. Bit lines 60 respectively conducted over or to the contact plugs 50
10 and capacitors are formed over these.